

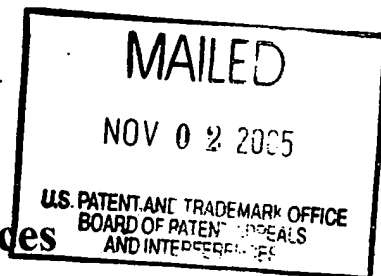


## United States Patent and Trademark Office

Under Secretary of Commerce for Intellectual Property and  
Director of the United States Patent and Trademark Office  
P.O. Box 1450  
Alexandria, Virginia 22313-1450  
[www.uspto.gov](http://www.uspto.gov)

BIRCH STEWART KOLASCH & BIRCH  
PO BOX 747  
FALLS CHURCH, VA 22040-0747

Paper No:  
Appeal No: 2006-0108  
Application: 09/980,620  
Appellant: Makoto Ozeki et al.



### Board of Patent Appeals and Interferences Docketing Notice

Application 09/980,620 was received from the Technology Center at the Board on September 29, 2005 and has been assigned Appeal No: 2006-0108.

A review of the file indicates that the following documents have been filed by appellant:

Appeal Brief filed on: February 20, 2004  
Reply Brief filed on: August 03, 2004  
Request for Hearing filed on: August 03, 2004

In all future communications regarding this appeal, please include both the application number and the appeal number.

The mailing address for the Board is:

**BOARD OF PATENT APPEALS AND INTERFERENCES  
UNITED STATES PATENT AND TRADEMARK OFFICE  
P.O. BOX 1450  
ALEXANDRIA, VIRGINIA 22313-1450**

The facsimile number of the Board is 571-273-0052. Because of the heightened security in the Washington D.C. area, facsimile communications are recommended. Telephone inquiries can be made by calling 571-272-9797 and should be directed to a Program and Resource Administrator.

By order of the Board of Patent Appeals and Interferences

S3	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with (2\$nm angstrom))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 17:47
S4	1	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with (2\$nm angstrom)) and (sidewall with silicide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 17:48
S5	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with (2\$nm angstrom))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 17:50
S6	39	((dual-gate (dual adj gate)) with (FET MOSFET MOS (field adj effect adj transistor))) and (channel with (2\$nm angstrom ""ANG.""))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 08:10